

**Amendment to the Abstract:**

The Abstract has been amended. A revised Abstract is attached.

A semiconductor laser device is provided that includes including: a type a first conductivity type, semiconductor substrate of a first conductivity type; a first conductivity type cladding layer of the first conductivity type provided on the semiconductor substrate; and an active layer provided on the cladding layer. of the first conductivity type, tThe active layer has having a super-lattice structure including a disordered region in a vicinity of a at least one cavity end face. A ; a first cladding layer of a second conductivity type is provided on the active layer, ; an etching stop layer of the second conductivity type is provided on the first cladding layer; and a second cladding layer of the second conductivity type is provided on the etching stop layer. T, the second cladding layer forming a ridge structure that extends, the ridge structure extending along a cavity length direction. An impurity and having a predetermined width. A concentration of an impurity in the etching stop layer in the vicinity of the at least one cavity end face is greater than a concentration of the impurity in the interior of a cavity and equal to or smaller than about  $2 \times 10^{18} \text{ cm}^{-3}$ .